



Code: 13A04804

B.Tech IV Year II Semester (R13) Advanced Supplementary Examinations July 2018

RF INTEGRATED CIRCUITS

(Electronics and Communication Engineering)

Time: 3 hours

Max. Marks: 70

PART – A

(Compulsory Question)

1 Answer the following: (10 X 02 = 20 Marks)

- Write the conditions for resonance in parallel RLC network.
- What is reflection coefficient in RF system?
- What is the relation between bandwidth and rise time for 1st order systems?
- What is figure of merit for a MOS devices?
- Define noise figure.
- What is mixer? Why the uses of mixer?
- What is meant by negative resistance oscillators?
- What is the difference between filter and loop filter?
- Define phase noise.
- What is CDMA?

PART – B

(Answer all five units, 5 X 10 = 50 Marks)

UNIT – I

- Explain in detail 'Pi' and 'T'-matching of a network.
 - Explain in detail the basic architecture of a RF system.

OR

- Compare parallel RLC and series RLC networks.
 - Explain about passive IC components interconnects in detail.

UNIT – II

- Draw and explain about shunt-series amplifier and write its applications.
 - Draw and explain about CS-amplifier for a single tuned amplifier.

OR

- Explain and derive bandwidth estimation using open circuit time constant and short circuit time constant.

UNIT – III

- Discuss about thermal noise, flicker noise and noise figure.
 - Explain in detail LNA design.

OR

- Explain about mixer design and sub sampling mixers.

UNIT – IV

- Explain about class A, AB RF power amplifier with neat diagrams.
 - Explain about charge pumps and loop filters.

OR

- Write short notes on:
 - Voltage controlled oscillators.
 - Negative resistance oscillators.

UNIT – V

- Explain about GSM radio architectures in detail with suitable diagram.
 - Discuss about integer-N synthesis and fractional frequency synthesis.

OR

- Write short notes on:
 - UMTS radio architectures.
 - CDMA radio architectures.

